

PRIMARY CHARACTERISTICS							
I _{T(AV)}	300 A						
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V						
V _{TM}	1.28 V						
I _{GT}	200 mA						
TJ	-40 °C to +125 °C						
Package	TO-118 (TO-209AE)						
Circuit configuration	Single SCR						

FEATURES

Phase Control Thyristors (Stud Version), 300 A

- International standard case TO-118 (TO-209AE)
- · Hermetic metal case with ceramic insulator
- Threaded studs UNF 3/4"-16UNF-2A or ISO M24 x 1.5
- · Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Designed and qualified for industrial level
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATING	S AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		300	А	
I _{T(AV)}	T _C	75	°C	
I _{T(RMS)}		470		
1	50 Hz	8000	А	
ITSM	60 Hz	8380		
l ² t	50 Hz	320	– kA²s	
1-1	60 Hz	292	KA2S	
V _{DRM} /V _{RRM}		400 to 2000	V	
tq	Typical	100	μs	
TJ		-40 to 125	°C	

ELECTRICAL SPECIFICATIONS

VOLTAGE R	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA					
	04	400	500						
	08	800	900						
VS-ST300S	12	1200	1300	50					
V3-313003	16	1600	1700	50					
	18	1800	1900						
	20	2000	2100						

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VS-ST300SPbF Series

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COMPLIANT

VS-ST300SPbF Series



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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	1	180° condu	ction, half sine v	wave	300	А
at case temperature	I _{T(AV)}				75	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 64 °C	case temperat	ure	470	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		8380	A
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		6730	
t = 8.3 ms reapplied		Sinusoidal half wave,	7040			
Marine 12 for fortun		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	320	kA ² s
	l ² t	t = 8.3 ms			292	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{BBM}		226	
		t = 8.3 ms	reapplied		207	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms t	o 10 ms, no volt	tage reapplied	3200	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.97	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J maxin$	num	0.98	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J maxin$	0.73	1115.2	
Maximum on-state voltage	V _{TM}	I _{pk} = 940 A,	$T_J = T_J maximu$	ım, t _p = 10 ms sine pulse	1.66	V
Maximum holding current	Ι _Η	T _ 05 °C	anada aunahi 1	2. V registive load	600	mA
Typical latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1	2 V resistive load	1000	IIIA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA			



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TRIGGERING							
PARAMETER	SYMBOL	TE	VAL	UNITS			
FANAMETEN	STMBOL		TEST CONDITIONS				
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10	0.0	w	
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	Α	
Maximum peak positive gate voltage	+ V _{GM}	T _J = T _J maximum,	2	20	V		
Maximum peak negative gate voltage	- V _{GM}	ij = ij maximum,	5	.0	v		
		T _J = -40 °C		200	-		
DC gate current required to trigger	I _{GT}	I _{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-		
		T _J = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-		
DC gate voltage required to trigger	V_{GT}	V _{GT}	T _J = 25 °C	12 V anoue to cathoue applied	1.8	3	V
		T _J = 125 °C			-		
DC gate current not to trigger	I _{GD}	T. T. movimum	Maximum gate current/voltage not to trigger is the maximum	10		mA	
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.	25	v	

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	- °C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	к/w		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.03	r\/ vv		
Mounting torque, ± 10 %		Non-lubricated threads	48.5 (425)	N · m (lbf · in)		
Approximate weight			535	g		
Case style		See dimensions - link at the end of datasheet	TO-118 (TO-	209AE)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS				
180°	0.011	0.008						
120°	0.013	0.014						
90°	0.017	0.018	$T_J = T_J$ maximum	K/W				
60°	0.025	0.026						
30°	0.041	0.042						

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

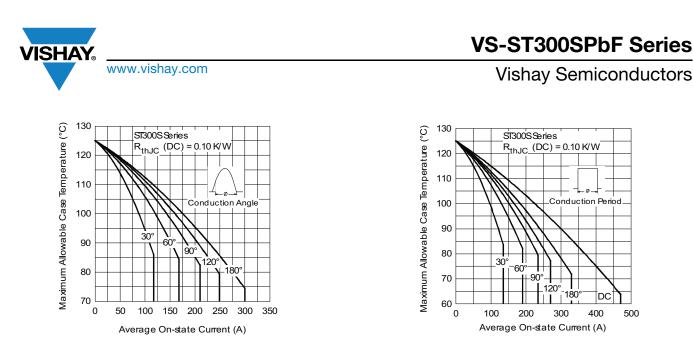


Fig. 1 - Current Ratings Characteristics

Fig. 2 - Current Ratings Characteristics

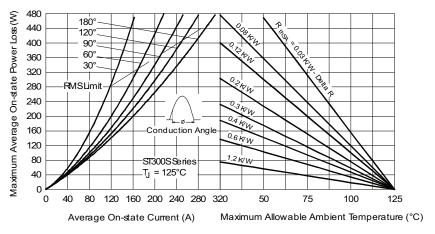


Fig. 3 - On-State Power Loss Characteristics

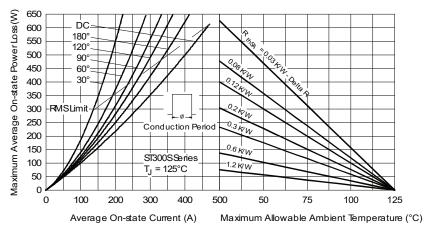


Fig. 4 - On-State Power Loss Characteristics

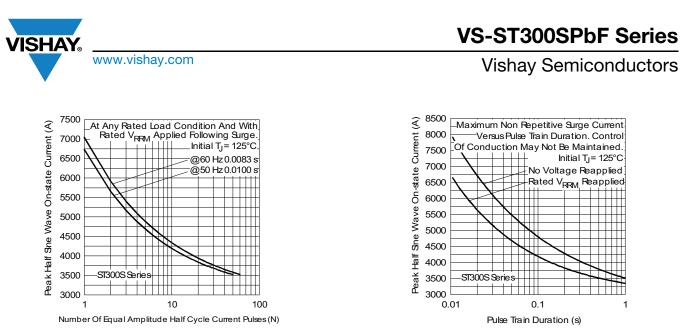


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

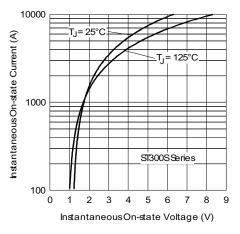


Fig. 7 - On-State Voltage Drop Characteristics

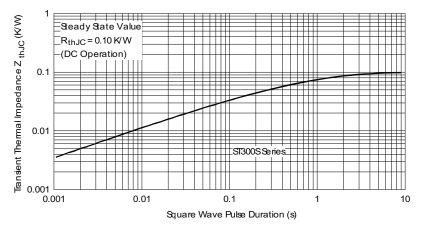


Fig. 8 - Thermal Impedance ZthJC Characteristics

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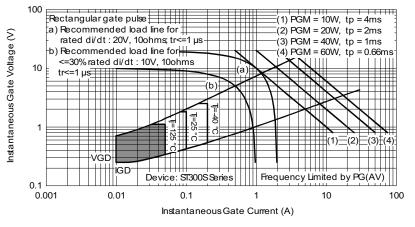


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	ST	30	0	S	20	Р	0	-	PbF
	1	2	3	4	5	6	7	8	9	10
	1 -	Visł	nay Sen	niconduo	ctors pro	oduct				
	2 -	Thy	ristor							
	3 -	Ess	ential pa	art numl	ber					
	4 -	0 =	Conver	ter grad	е					
	5 -	S =	Compre	ession b	onding s	stud				
	6 -	Volt	age coo	de x 100	= V _{RRM}	l (see V	oltage F	Ratings	table)	
	7 -	P =	stud ba	se 3/4"	16UNF-	2A threa	ads			
		M =	stud ba	ase metr	ic thread	ds (M24	x 1.5)			
	8 -	0 =	Eyelet t	erminals	s (gate a	and auxi	liary ca	thode le	eads)	
		1 =	Fast-on	termina	als (gate	and au	xiliary c	athode	leads)	
					erminal 3					
	9 -			-	ne = 50)	
					= 1000 V					
	10 -	Nor	ne = Sta	ndard p	roductio	n				
	 			l (Pb)-fro						
				. ,						

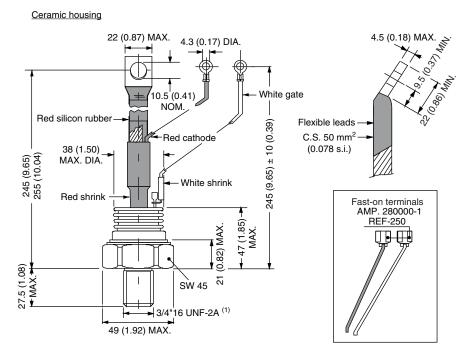
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95084				



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TO-209AE (TO-118)

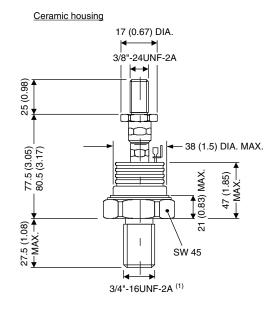
DIMENSIONS - TO-209AE (TO-118) in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length screw 21 (0.83) maximum

DIMENSIONS - TO-209AE (TO-118) WITH TOP THREAD TERMINAL 3/8" in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length screw 21 (0.83) maximum



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